

High-voltage Switching Transistor

(Camera strobes and Telephone, Power supply) (−400V, −0.1A)

2SA1759

● Features

- 1) High breakdown voltage. ($BV_{CEO} = -400V$)
- 2) Low saturation voltage, typically $V_{CE(sat)} = -0.2V$ at $I_C / I_E = -20mA / -2mA$.
- 3) High switching speed, typically $t_f = 1 \mu s$ at $I_C = 100mA$.
- 4) Wide SOA (safe operating area).
- 5) Complements the 2SA4505.

● Packaging specifications and hFE

Type	2SA1759
Package	MPT3
hFE	P
Marking	AH*
Code	T100
Basic ordering unit (pieces)	3000

* Denotes hFE

● Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	−400	—	—	V	$I_C = -50 \mu A$
Collector-emitter breakdown voltage	BV_{CEO}	−400	—	—	V	$I_C = -1mA$
Emitter-base breakdown voltage	BV_{EBO}	−7	—	—	V	$I_E = -50 \mu A$
Collector cutoff current	I_{CBO}	—	—	−10	μA	$V_{CB} = -400V$
Emitter cutoff current	I_{EBO}	—	—	−10	μA	$V_{EB} = -6V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	−0.2	−0.5	V	$I_C / I_E = -20mA / -2mA$
Base-emitter saturation voltage	$V_{BE(sat)}$	—	—	−1.2	V	$I_C / I_E = -20mA / -2mA$
DC current transfer ratio	hFE	82	—	180	—	$V_{CE} = -10V, I_C = -10mA$
Transition frequency	fT	—	12	—	MHz	$V_{CE} = -10V, I_E = 10mA, f = 5MHz$
Output capacitance	Cob	—	13	—	pF	$V_{CB} = -10V, I_E = 0A, f = 1MHz$
Turn-on time	t _{on}	—	0.7	—	μs	$I_C = -100mA, R_L = 1.5k\Omega$
Storage time	t _{stg}	—	1.8	—	μs	$I_{B1} = -I_{B2} = -10mA$
Fall time	t _f	—	1	—	μs	$V_{CC} \sim -150V$

(96-97-A324)

Power Transistor (400V, 0.1A)

2SC4505 / 2SC4620

● Features

- 1) High breakdown voltage. ($BV_{CEO} = 400V$)
- 2) Low saturation voltage, typically $V_{CE(sat)} = 0.05V$ at $I_C / I_E = 10mA / 1mA$.
- 3) High switching speed, typically $t_f = 1.7 \mu s$ at $I_C = 100mA$
- 4) Complements the 2SC4505 and the 2SA1759.

● Packaging specifications and hFE

Type	2SC4505	2SC4620
Package	MPT3	ATV
hFE	PQ	Q
Marking	CE*	—
Code	T100	TV2
Basic ordering unit (pieces)	1000	2500

* Denotes hFE

● Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	400	—	—	V	$I_C = 50 \mu A$
Collector-emitter breakdown voltage	BV_{CEO}	400	—	—	V	$I_C = 1mA$
Emitter-base breakdown voltage	BV_{EBO}	7	—	—	V	$I_E = 50 \mu A$
Collector cutoff current	I_{CBO}	—	—	10	μA	$V_{CB} = 400V$
Emitter cutoff current	I_{EBO}	—	—	10	μA	$V_{EB} = 6V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	0.05	0.5	V	$I_C = 10mA, I_E = 1mA$
Base-emitter saturation voltage	$V_{BE(sat)}$	—	—	1.5	V	$I_C = 10mA, I_E = 1mA$
DC current transfer ratio	hFE	82	—	270	—	$V_{CE} / I_C = 10V / 10mA$
Transition frequency	fT	—	20	—	MHz	$V_{CE} = 10V, I_E = -10mA, f = 10MHz$
Output capacitance	Cob	—	7	—	pF	$V_{CB} = 10V, I_E = 0A, f = 1MHz$
Turn-on time	t _{on}	—	1	—	μs	$I_C = 100mA$
Storage time	t _{stg}	—	5.5	—	μs	$I_{B1} = -I_{B2} = 10mA$
Fall time	t _f	—	1.7	—	μs	$V_{CC} \sim -150V$

(96-178-C300)

● Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	−400	V
Collector-emitter voltage	V_{CEO}	−400	V
Emitter-base voltage	V_{EBO}	−7	V
Collector current	I_C	−0.1	A (DC)
		−0.2	A (Pulse) *1
Collector power dissipation	P_C	0.5	W
		2 *2	
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	−55~+150	°C

*1 Single pulse, P_w=100ms

*2 When mounted on a 40×40×0.7 mm ceramic board.

● Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	400	V
Collector-emitter voltage	V_{CEO}	400	V
Emitter-base voltage	V_{EBO}	7	V
Collector current	I_C	0.1	A
		0.2	A *
Collector power dissipation	P_C	0.5	W
		1	
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	−55~+150	°C

* Single pulse P_w=20ms Duty=1 / 2